

**isc N-Channel MOSFET Transistor**
**AOT470**
**FEATURES**

- Drain Current  $-I_D=100A@ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}=75V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 10.5m\ \Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**DESCRIPTION**

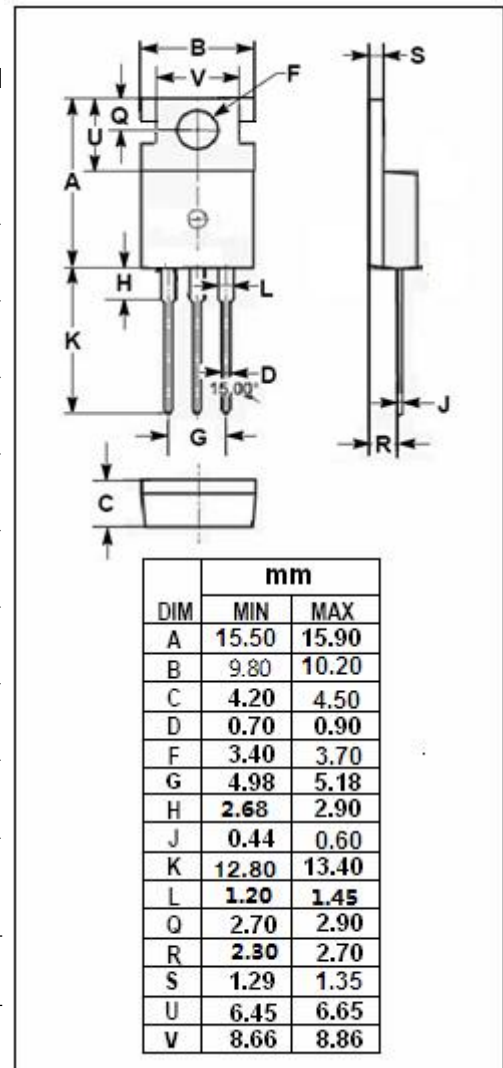
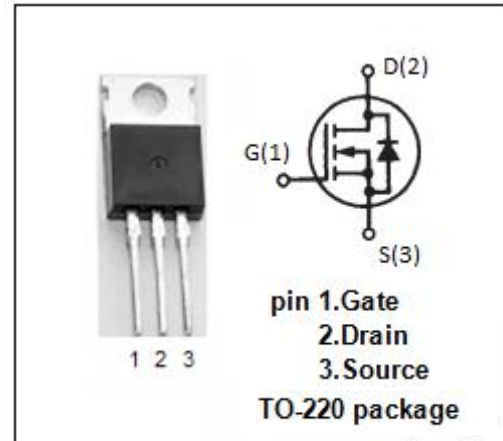
- Designed for use in switch mode power supplies and general purpose applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

| SYMBOL    | PARAMETER                            | VALUE    | UNIT       |
|-----------|--------------------------------------|----------|------------|
| $V_{DSS}$ | Drain-Source Voltage                 | 75       | V          |
| $V_{GS}$  | Gate-Source Voltage-Continuous       | $\pm 25$ | V          |
| $I_D$     | Drain Current-Continuous             | 100      | A          |
| $I_{DM}$  | Drain Current-Single Pluse           | 200      | A          |
| $P_D$     | Total Dissipation @ $T_C=25^\circ C$ | 268      | W          |
| $T_J$     | Max. Operating Junction Temperature  | -55~175  | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                  | -55~175  | $^\circ C$ |

**THERMAL CHARACTERISTICS**

| SYMBOL        | PARAMETER                            | MAX  | UNIT         |
|---------------|--------------------------------------|------|--------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 0.56 | $^\circ C/W$ |



## isc N-Channel MOSFET Transistor

## AOT470

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS   | MIN | MAX    | UNIT |
|----------------------|---------------------------------|--|-----|--------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA   | 75  |        | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = 5V; I <sub>D</sub> = 0.25mA  | 3.6 | 5.0    | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 30A  |     | 10.5   | mΩ   |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±25V; V <sub>DS</sub> = 0  |     | ± 1    | uA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 75V; V <sub>GS</sub> = 0<br>V <sub>DS</sub> = 75V; V <sub>GS</sub> = 0@T <sub>J</sub> = 55°C |     | 1<br>5 | μ A  |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = 1A; V <sub>GS</sub> = 0   |     | 1      | V    |

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